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Computational study of the dielectric properties of $[\mathrm{La,Sc}]_2\mathrm{O}_3$ solid solutions

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First-principles calculations were used to compute the dielectric permittivities of hypothetical $[\mathrm{La,Sc}]_2\mathrm{O}_3$ solid solutions in the cubic (bixbyite) and hexagonal $\mathrm{La_2O_3}$ phases. Dielectric enhancement is predicted at small Sc concentrations due to the rattling ion effect. Similar calculations for a model amorphous $\mathrm{La_2O_3}$ structure show little change in permittivity when a small amount of Sc is substituted for La. In this case, the local environment around the Sc changes in a way that compensates for the rattling ion effect.

High permittivity ("high κ") dielectric materials for microelectronics applications require a combination of properties, including a permittivity κ larger than that of amorphous $\mathrm{SiO_2}$ ($\kappa = 3.9$), thermodynamic stability in contact with Si, and sufficient band offsets with respect to Si.[1] While high-κ dielectrics based on $\mathrm{HfO_2}$ have been incorporated into commercial computer chips,[2] other "higher-κ" materials continue to be actively investigated,[3] as future Metal-Oxide-Semiconductor Field-Effect Transistor (MOSFET) scaling will likely require dielectrics with higher κ than $\mathrm{HfO_2}$.[4] An additional concern for dielectrics for MOSFET applications is whether the dielectric is amorphous. Amorphous dielectrics are considered superior, as microcrystalline dielectrics can exhibit significant charge leakage and ionic diffusion due to grain boundaries.[1] On the other hand, crystalline dielectrics are still of interest, as epitaxial dielectric growth[3] would avoid the above problems.

Early compilations of candidate high-κ materials indicated that $\mathrm{La_2O_3}$ has higher permittivity than $\mathrm{HfO_2}$,[1] thus much attention on higher-κ materials has focused on $\mathrm{La_2O_3}$ and other $R_2\mathrm{O}_3$-based materials (R = rare earth). High permittivities have been reported in both single component $R_2\mathrm{O}_3$ compounds, such as $\mathrm{Sm_2O_3}$,[5] and in stoichiometric $R\mathrm{ScO_3}$ compounds, such as $\mathrm{GdScO_3}$ and $\mathrm{DyScO_3}$.[6] This work explores a possible way to further enhance the permittivity of rare-earth dielectrics: nonstoichiometric substitution of Sc for the R ion. This idea is inspired by recent theoretical work on the $\mathrm{Ba}_{1-x}\mathrm{Ca}_x\mathrm{ZrO_3}$ (BCZO) perovskite system.[7] BCZO has a dielectric anomaly, where the permittivity is higher for intermediate compositions than for either endmember, reaching a maximum in the range $x \approx 0.1$ to 0.2.[8,9] The enhancement in permittivity is due to a "rattling ion" effect: the smaller Ca ion in the lattice site of the larger Ba ion is relatively loosely bound and can thus move farther under an applied electric field. A similar effect might be expected when a small Sc ion substitutes isovalently for a larger R ion in $R_2\mathrm{O}_3$ compounds. The largest R^{3+} ion is La^{3+} (Ref. 10); thus we explore the dielectric properties of the $\mathrm{La}_{2-2x}\mathrm{Sc}_{2x}\mathrm{O}_3$ (LSO) solid solution system in this work.

$\mathrm{La_2O_3}$ has two room-temperature polymorphs: a cubic (c) bixbyite phase and a hexagonal (h) phase.[10,11] Due to the small difference in energy between c-$\mathrm{La_2O_3}$ and h-$\mathrm{La_2O_3}$ (which is thermodynamically stable at sintering temperatures of order 1000 °C), it is not clear which phase is the most stable at room temperature.[10] We thus explore both structures. $\mathrm{Sc_2O_3}$ has the cubic bixbyite structure at room temperature. LSO has one ordered intermediate phase,[10] with the perovskite (p) structure.[12]

We ran first principles calculations on the 40-atom primitive cell for c-$\mathrm{La_2O_3}$ cell, and on a 40 atom h-$\mathrm{La_2O_3}$ supercell (each cell parameter doubled), for both pure $\mathrm{La_2O_3}$ and for the same cells with one Sc substituted for La ($x = 0.0625$). The initial atomic positions were taken from the literature.[11] Additional calculations were performed for: (1) c-LSO with $x = 0.25$, to test the linearity of κ vs. x; (2) c-LSO with $x = 0.9375$ ("reverse" Sc → La substitution); (3) ideal p-$\mathrm{LaScO_3}$; (4) a model for amorphous $\mathrm{La_2O_3}$, and (5) a model for amorphous LSO (a-LSO) with $x = 0.0625$. All calculations were performed at the experimental volume or the volume given by Vegard's law: $V = (1-x)V_{\mathrm{La_2O_3}} + x\,V_{\mathrm{Sc_2O_3}}$.

Structural relaxations and dielectric constant calcula-

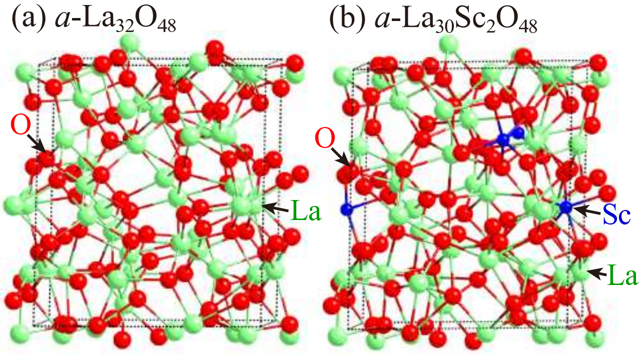
(a) a-$\mathrm{La_{32}O_{48}}$
O
La
(b) a-$\mathrm{La_{30}Sc_2O_{48}}$
O
Sc
La

FIG. 1: (Color online) Relaxed models for (a) amorphous $\mathrm{La_2O_3}$ and (b) $\mathrm{La}_{2-2x}\mathrm{Sc}_{2x}\mathrm{O}_3$ ($x = 0.0625$).

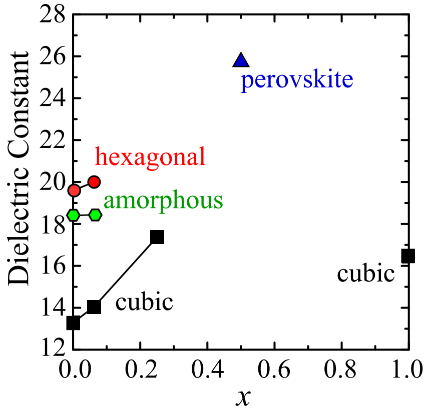

FIG. 2: (Color online) Comparative computed dielectric constant for $La_{2-2x}Sc_{2x}O_3$ structures studied in this work.

TABLE I: Calculated dielectric constant ($\kappa = \kappa^{\mathrm{el}} + \kappa^{\mathrm{ion}}$) and band gap at Γ ($E_{\mathrm{g}}$) for $La_{2-2x}Sc_{2x}O_3$ structures studied in this work.

x	κ	κ^{ion}	κ^{el}	E_{g} (eV)
Cubic bixbyite				
0	13.29	9.13	4.17	3.67
0.0625	14.04	9.83	4.22	3.36
0.25	17.37	13.04	4.33	2.55
0.9375	–	–	4.19	3.63
1	16.46	12.33	4.13	3.87
Hexagonal				
0	19.60	14.88	4.72	3.73
0.0625	20.00	15.31	4.69	3.56
Amorphous				
0	18.42	14.00	4.42	2.90
0.0625	18.43	14.03	4.39	2.96
Perovskite				
0.5	25.68	20.96	4.72	3.91

tions were performed using the density functional theory code PHASE.[13] Ultrasoft pseudopotentials[14] were used, with the PBE generalized gradient approximation[15] for the exchange-correlation functional, and a plane wave basis set with a 36 Rydberg cutoff energy for the electronic wavefunctions. Brillouin zone integrations were performed with the Γ point only for the force calculations, and were done with appropriate grids for the electronic dielectric constant and the Berry phase calculations. All structures were relaxed until the force on each atom was smaller than 0.002 Ry/Bohr. For c-La_2O_3, there are two inequivalent La positions: 8(b) and 24(d) (Ref. 11; modern convention for space group $Ia\bar{3}$ Wyckoff positions from Ref. 16). At both $x = 0.0625$ and $x = 0.9375$, the lowest energy is found when the minority species is on the 8(b) site. Because a single occupied 8(b) is lower in energy than 24(d), it seems reasonable to assume that, for lowest energy configurations, the 8(b) sites fill with Sc before the 24(d) sites. For the $x = 0.25$ calculation, therefore it was assumed that lowest energy occurs when the 8(b) site is fully occupied.

A model for the La_2O_3 amorphous phase was generated by the *ab initio* molecular dynamics "melt and quench" technique.[17] A 80-atom cubic La_2O_3 cell was "melted" at 3000 K until the root mean square displacement of oxygens from their original positions was greater than the original oxygen-oxygen near-neighbor distance. Then the cell was quenched for 1 ps of simulation time at 1000 K. The lowest energy structure during this run was recorded, and subsequently a full relaxation (cell shape and atomic positions) was performed to obtain an a-La_2O_3 model. (The melt-and-quench technique was done using the VASP package[18] with projected augmented wave functions[19] and the local density approximation for exchange-correlation; the final relaxation and subsequent steps used PHASE, as above.) After this relaxation, bond valence sums[20,21] were computed to identify the most underbonded La as the most favorable positions for Sc. The Sc was placed on the most underbonded La site because the smaller ionic radius of Sc favors the lower coordination number. The two most underbonded La separated by more than $a/2$ were replaced by Sc, and the structure then fully relaxed under the new cell volume to obtain a model for a-LSO; $x = 0.0625$. The procedure insures that the a-LSO model is as similar as possible to a-La_2O_3 model for direct comparison of their properties (Fig. 1).

The dielectric properties were computed using the frozen phonon method, as discussed in Ref. 22. Briefly, the static dielectric constant of a crystal is given by

$$\kappa = \kappa^{\mathrm{el}} + \kappa^{\mathrm{ion}} = \kappa^{\mathrm{el}} + C \sum_{\mu} \frac{{Z_\mu}^2}{{\omega_\mu}^2}, \qquad (1)$$

where C is a constant, κ^{el} the electronic contribution to the dielectric constant, κ^{ion} the ionic contribution, Z_μ the dipole moment associated with mode μ and ω_μ its frequency. Aside from obtaining the dielectric constants, the breakdown of the lattice dielectric contribution over individual modes allows one to find the origins of any dielectric anomaly that is due to lattice effects. A rattling ion effect will show up as a significant contribution to κ from a mode with low frequency and/or high Z_μ that is located on or near the rattling ion.

Fig. 2 shows the dielectric constant computed for each structure. Table I shows, in addition, κ^{el}, κ^{ion}, and the calculated bandgaps. For small x, the dielectric constants of both c-LSO and h-LSO are higher than the weighted average of the endmember La_2O_3 and Sc_2O_3 compounds. Phonon density of states calculations (Fig. 3) show that, as x increases, the frequencies of the modes around 200 cm^{-1} to 300 cm^{-1} that contribute significantly to the dielectric constant decrease. The dielectric constant is thus enhanced, per Eq. (1).[23] Analysis of these lower-frequency phonons shows that the eigenvectors are dominated by Sc motion coupled to motion of its nearest neighbor O octahedron in the opposite direction. We therefore conclude that the enhancement of κ is due to

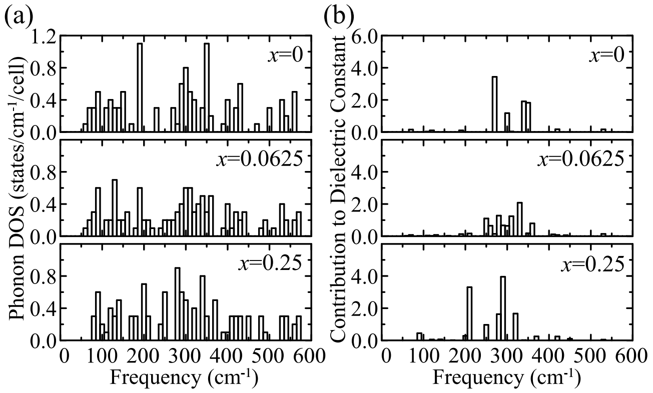

FIG. 3: (a) Comparative phonon density of states for c-$La_{2-2x}Sc_{2x}O_3$ versus x. (b) Contribution of phonons to dielectric constant, versus x, binned by 10 cm^{-1} range of frequency.

the rattling ion effect. This hypothetical effect is distinct from the enhancement of permittivity due to rare-earth doping of HfO_2, which is believed to result from the stabilization of the HfO_2 tetragonal phase relative to the monoclinic one.[24] For the h-LSO case, the substituted Sc atom displaces along the hexagonal c axis to optimize the structure. Tight (0.201 nm) and weak (0.304 nm) Sc-O bonds are formed. As a result, Sc moves more easily along the c axis, but is more rigid in the ab plane. The κ_{cc} component is enhanced, while κ_{aa} and κ_{bb} are reduced. Overall, κ is enhanced. When a small amount of La is substituted for Sc in c-Sc_2O_3, the κ^{el} increases, which we attribute to the bandgap reduction (Table I), but κ^{ion} was not calculated, as a mode with imaginary frequency (*i.e.* an instability) appears. In other words, a small amount of La substitution is predicted to break the cubic symmetry. The relative increase in κ with composition is less than that found for BCZO,[7] and the dielectric constant predicted at $x = 0.25$ does not exceed that computed for the intermediate perovskite $LaScO_3$ phase. Nonetheless, if a phase that is close in composition to R_2O_3 is desired, our results suggest a way to increase the permittivity with relatively small doping of Sc. Furthermore, if it were possible to substitute a small amount of Sc on the A site of a RScO$_3$ perovskite (an isostructural analog to BCZO) without destabilizing the perovskite phase, the rattling ion effect might yield a permittivity even higher than for stoichiometric p-RScO$_3$ compounds.

Our results predict that κ for amorphous La_2O_3 is higher than for c-La_2O_3 but smaller than for h-La_2O_3. Delugas *et al.* predict a similar permittivity enhancement for amorphous Sc_2O_3 with respect to c-Sc_2O_3.[25] In contrast to the crystalline cases studied, the computed dielectric constant of a-La_2O_3 does not increase when a small amount of Sc is substituted for La. We explain the lack of any rattling ion effect as a consequence of different Sc and La local environments in a-LSO. Upon relaxation, the Sc ions have on average 5.0 oxygen neighbors at an average distance of 0.208 nm, while the La ions have on average 6.0 oxygen neighbors at an average distance of 0.246 nm. The results suggest that the local environment around Sc in a-LSO "tightens up" relative to the typical La local environment in a way that compensates for the rattling ion effect.

To summarize, small substitution of Sc for La in crystalline La_2O_3 compounds is predicted to cause an anomalous increase in the dielectric constant due to the rattling ion effect: a small Sc ion in a loose environment can move farther in an applied electric field. For amorphous La_2O_3, we predict no anomalous increase, as La and Sc have different local environments in this case.

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